



## **ISC Silicon NPN Power Transistor**

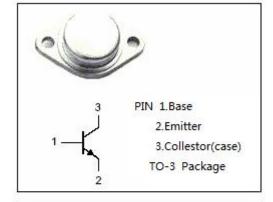
#### **DESCRIPTION**

- High Speed- $t_f$ = 0.5  $\mu$  s (Max)
- · Low Saturation Voltage- $V_{CE(sat)} \leq$  2.5V@  $I_C$ = 20A
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device Performance and reliable operation.



### **APPLICATIONS**

· Designed for use in switching regulators, inverters, wideband amplifiers and power oscillators in industrial and commercial applications.

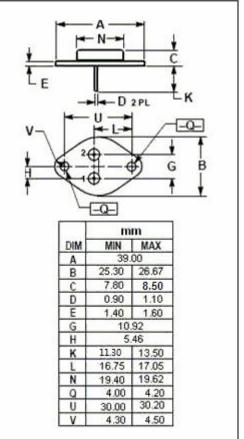


# ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector- Base Voltage	150	V
V <sub>CEO</sub>	Collector-Emitter Voltage	90	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
Ic	Collector Current-Continuous	20	Α
l <sub>Β</sub>	Base Current-Continuous 5		Α
Pc	Collector Power Dissipation @T <sub>C</sub> =25℃	140	W
TJ	Junction Temperature	200	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-65~200	$^{\circ}$ C

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	1.25	°C/W



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2N5038

### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT				
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ; I <sub>B</sub> = 0	90		V				
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 20A; I <sub>B</sub> = 5.0A		2.5	V				
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 20A; I <sub>B</sub> = 5.0A		3.3	V				
I <sub>CEX</sub>	Collector Cutoff Current	V <sub>CE</sub> = 150V; V <sub>BE(off)</sub> =1.5V		0.5	mA				
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5.0V; I <sub>C</sub> = 0 V <sub>EB</sub> = 7.0V; I <sub>C</sub> = 0		5 50	mA				
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 12A ; V <sub>CE</sub> = 5V	20	100					
Switching times									
tr	Rise Time			0.5	μS				
ts	Storage Time	V <sub>CC</sub> = 30V, I <sub>C</sub> = 12A , I <sub>B1</sub> = -I <sub>B2</sub> = 1.2A,		1.5	μ <b>S</b>				
t <sub>f</sub>	Fall Time			0.5	μS				

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